

UTT15N03

Power MOSFET

15A, 30V N-CHANNEL
ENHANCEMENT MODE

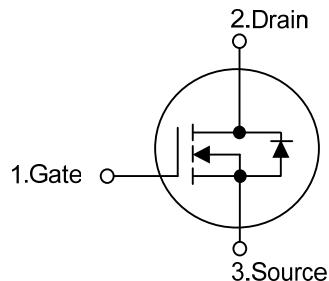
■ DESCRIPTION

The **UTT15N03** uses UTC's advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

- * $R_{DS(ON)} < 12 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=15\text{A}$
- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

■ SYMBOL



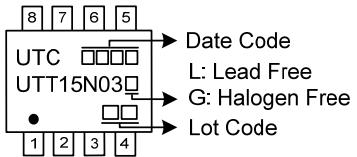
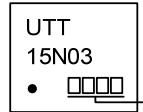
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTT15N03L-S08-R	UTT15N03G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel
UTT15N03L-K08-3030-R	UTT15N03G-K08-3030-R	DFN3030-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT15N03G-S08-R 	(1) R: Tape Reel (2) S08: SOP-8, K08-3030: DFN3030-8 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

SOP-8	DFN3030-8
 <p>8 7 6 5 UTC □□□ UTT15N03□ • □□ 1 2 3 4</p> <p>Date Code L: Lead Free G: Halogen Free Lot Code</p>	 <p>UTT 15N03 • □□□□ Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	I_D	15	A
Pulsed Drain Current	I_{DM}	40	A
Avalanche Current	I_{AR}	20	A
Repetitive avalanche energy $L=0.1\text{mH}$	E_{AR}	50	mJ
Power Dissipation	SOP-8	1.6	W
	DFN3030-8	2.0	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
 Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating : Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction-to-Ambient	SOP-8	78	$^\circ\text{C}/\text{W}$
	DFN3030-8	62.5	$^\circ\text{C}/\text{W}$

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

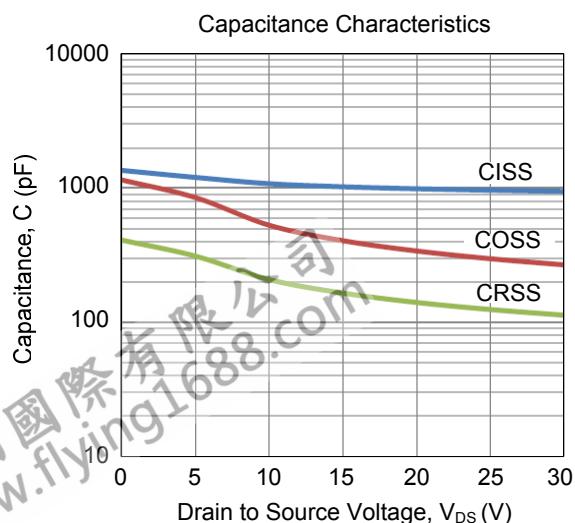
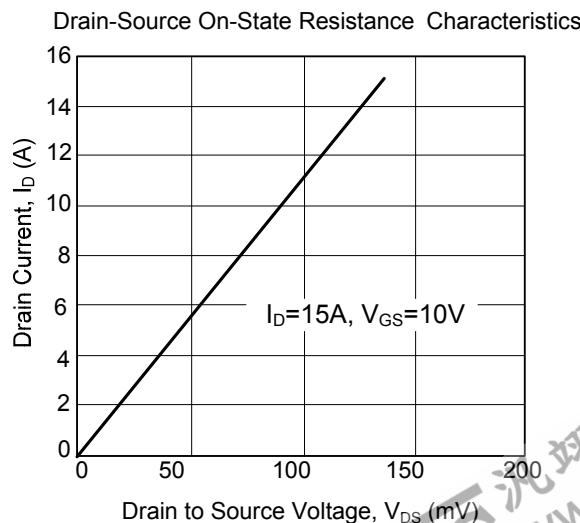
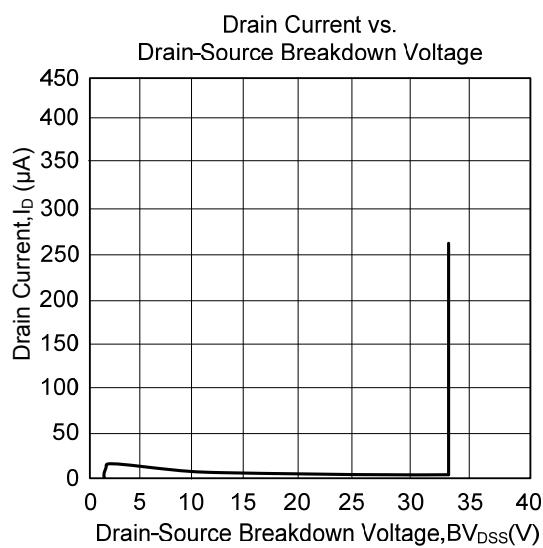
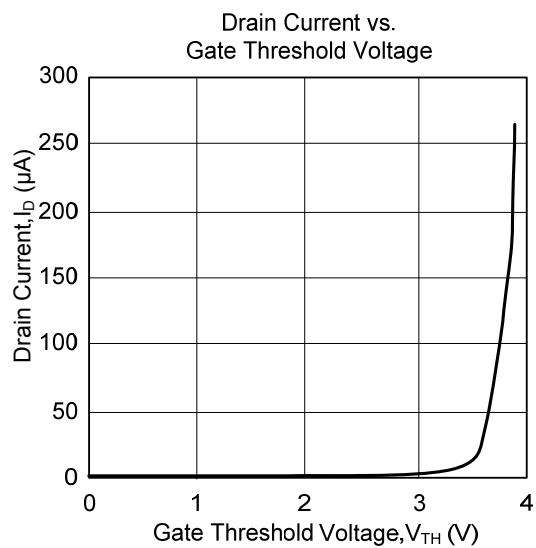
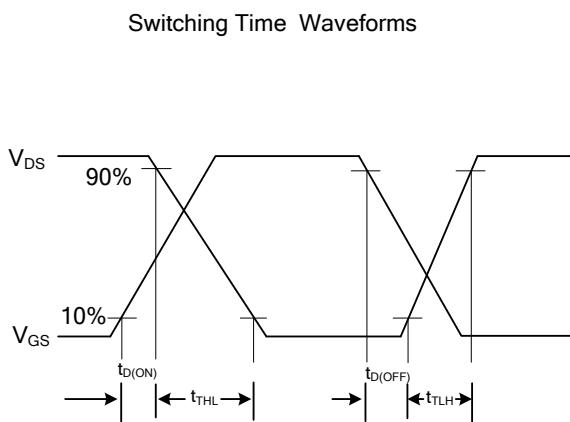
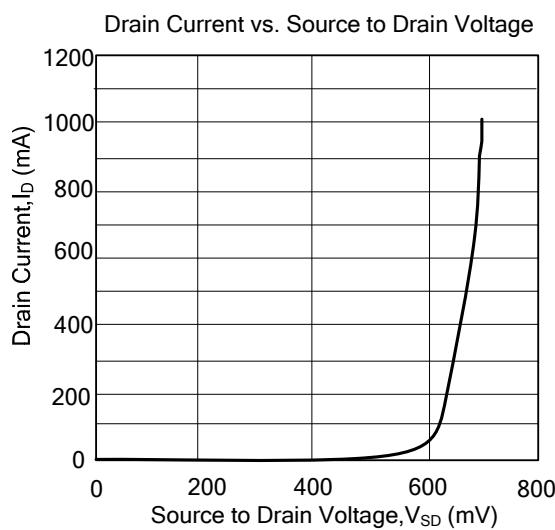
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=24\text{V}, V_{\text{GS}}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm20\text{V}$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	1.0		3.0	V
On State Drain Current	$I_{\text{D(ON)}}$	$V_{\text{DS}}=5\text{V}, V_{\text{GS}}=10\text{V}$	40			A
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_D=15\text{A}$			12	$\text{m}\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		1024		pF
Output Capacitance	C_{OSS}			400		pF
Reverse Transfer Capacitance	C_{RSS}			165		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=10\text{V}, I_D=1\text{A}$		130		nC
Gate Source Charge	Q_{GS}			23		nC
Gate Drain Charge	Q_{GD}			82		nC
Turn-ON Delay Time	$t_{\text{D(ON)}}$	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=15\text{V}, R_L=15\Omega, R_G=3\Omega$		68		ns
Turn-ON Rise Time	t_R			104		ns
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			344		ns
Turn-OFF Fall-Time	t_F			221		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				4	A
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}, V_{\text{GS}}=0\text{V}$		0.71	1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=15\text{A}, dI/dt=100\text{A}/\mu\text{s}$		210		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=15\text{A}, dI/dt=100\text{A}/\mu\text{s}$		0.58		μC

Notes: 1. The data tested by pulsed, pulse width $\leq300\mu\text{s}$, duty cycle $\leq2\%$.

2. The power dissipation is limited by 150°C junction temperature.

■ TYPICAL CHARACTERISTICS



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